

General Description

The MY50P03NE5 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

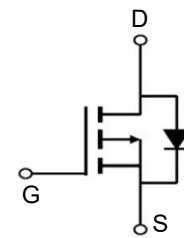
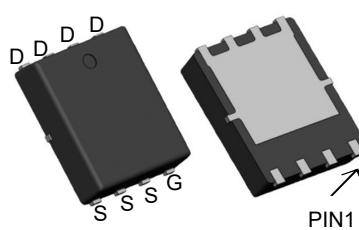


Features

X_{FUU}	-30	X
I_F	-50	C
$T_{FUQP+CVXI U? 10X_+}$	11.5	o á
$T_{FUQP+CVXI U? 4.5X_+}$	18	o á

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY50P03NE5	PDFN5*6-8L	NULL	5000

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_c=25^\circ\text{C}$)	I_D	-50	A
Drain Current-Continuous ($T_c=100^\circ\text{C}$)		-24	
Drain Current-Pulsed ^(Note 1)	IDM	-80	A
Maximum Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	3	W
Maximum Power Dissipation ($T_c=100^\circ\text{C}$)		1.3	
Single pulse avalanche energy ^(Note 5)	EAS	231	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C
Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	41.67	°C/W

Electrical Characteristics (T_j=25 °C, unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-3	V
Drain-Source On-State Resistance	R _{D(S)} (ON)	V _{GS} =-10V, I _D =-10A	-	11.5	15	mΩ
		V _{GS} =-4.5V, I _D =-7A	-	18	25	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-10A	-	20	-	S
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	1750	-	PF
Output Capacitance	C _{oss}		-	215	-	PF
Reverse Transfer Capacitance	C _{rss}		-	180	-	PF
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-10A, V _{GS} =-10V, R _{GEN} =1Ω	-	9	-	nS
Turn-on Rise Time	t _r		-	8	-	nS
Turn-Off Delay Time	t _{d(off)}		-	28	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V	-	24	-	nC
Gate-Source Charge	Q _{gs}		-	3.5	-	nC
Gate-Drain Charge	Q _{gd}		-	6	-	nC
Diode Forward Current (Note 2)	I _s		-	-	-12	A
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _s =-12A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: T_j=25 °C, V_{DD}=-15V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=-34A

Typical Characteristics

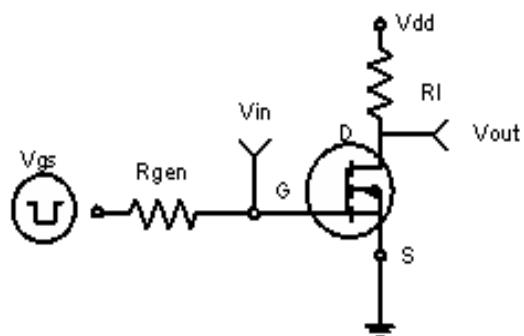


Figure 1:Switching Test Circuit

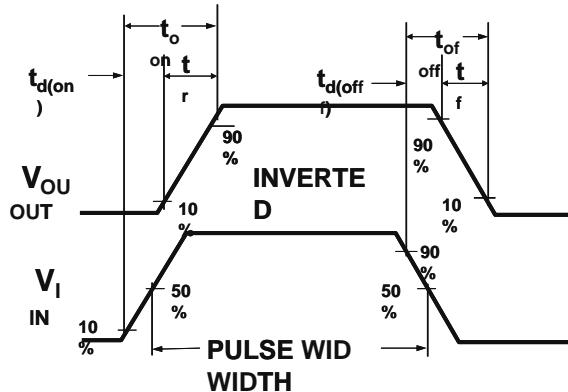


Figure 2:Switching Waveforms

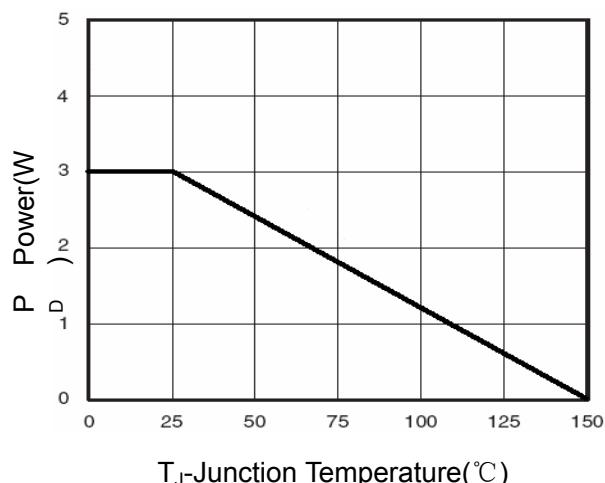


Figure 3 Power Dissipation

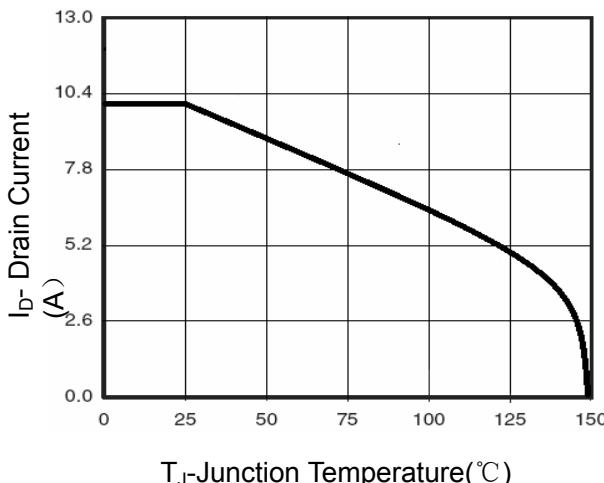


Figure 4 Drain Current

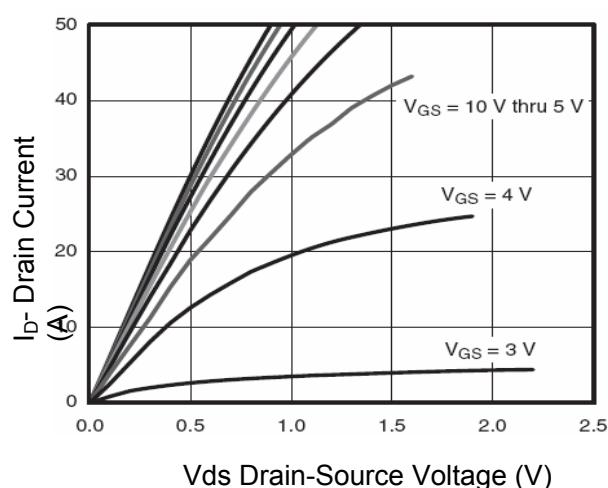


Figure 5 Output Characteristics

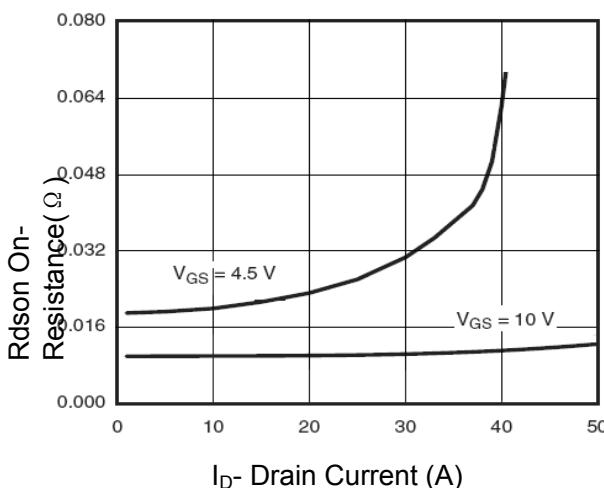


Figure 6 Drain-Source On-Resistance

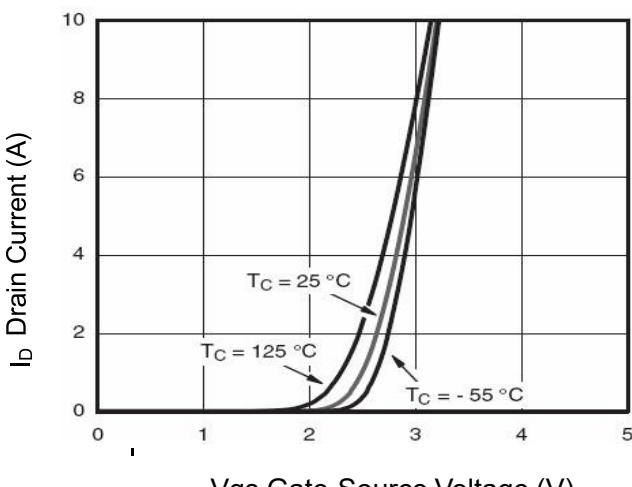


Figure 7 Transfer Characteristics

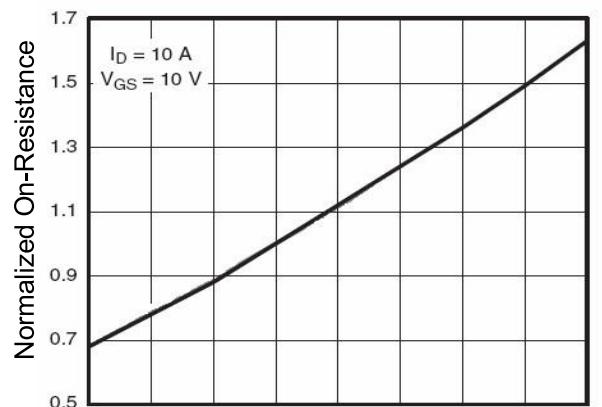


Figure 8 Drain-Source On-Resistance

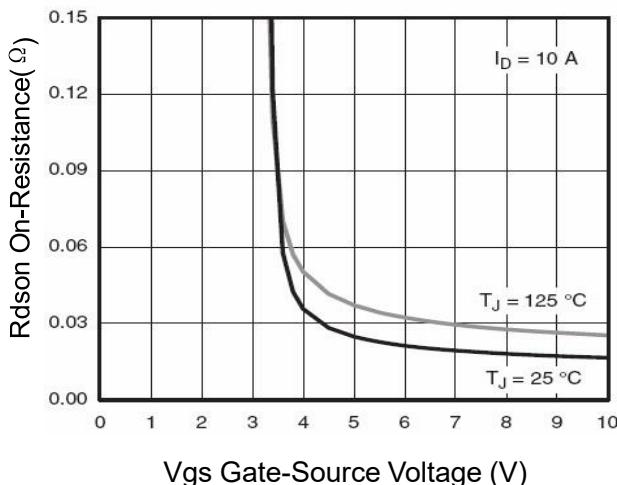


Figure 9 $R_{DS(on)}$ vs V_{GS}

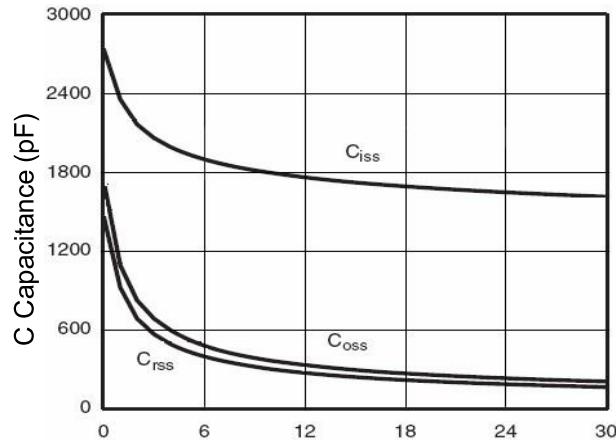


Figure 10 Capacitance vs V_{DS}

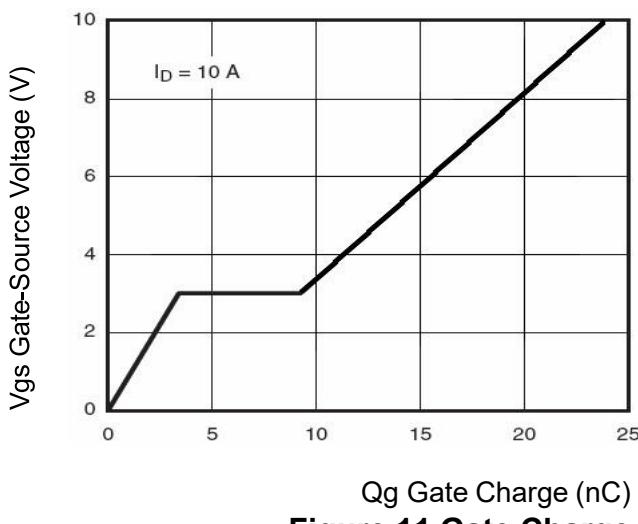


Figure 11 Gate Charge

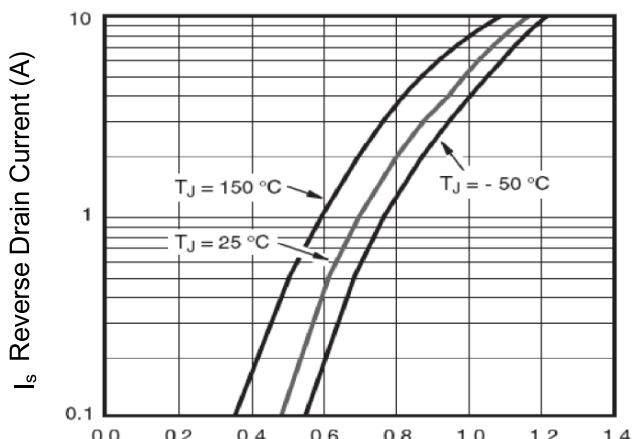
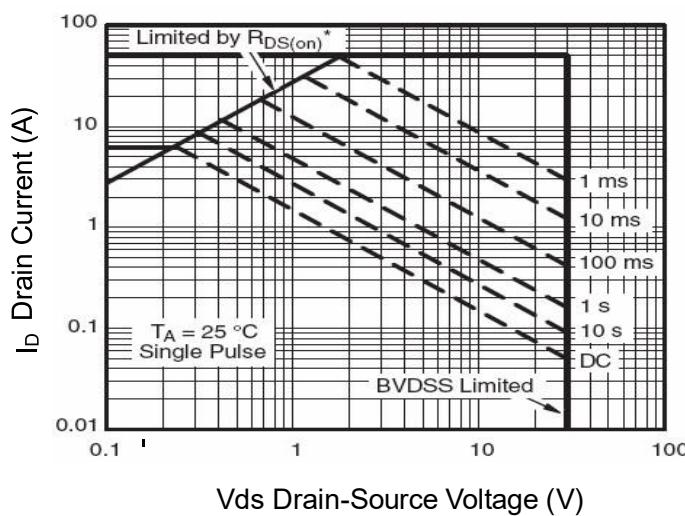
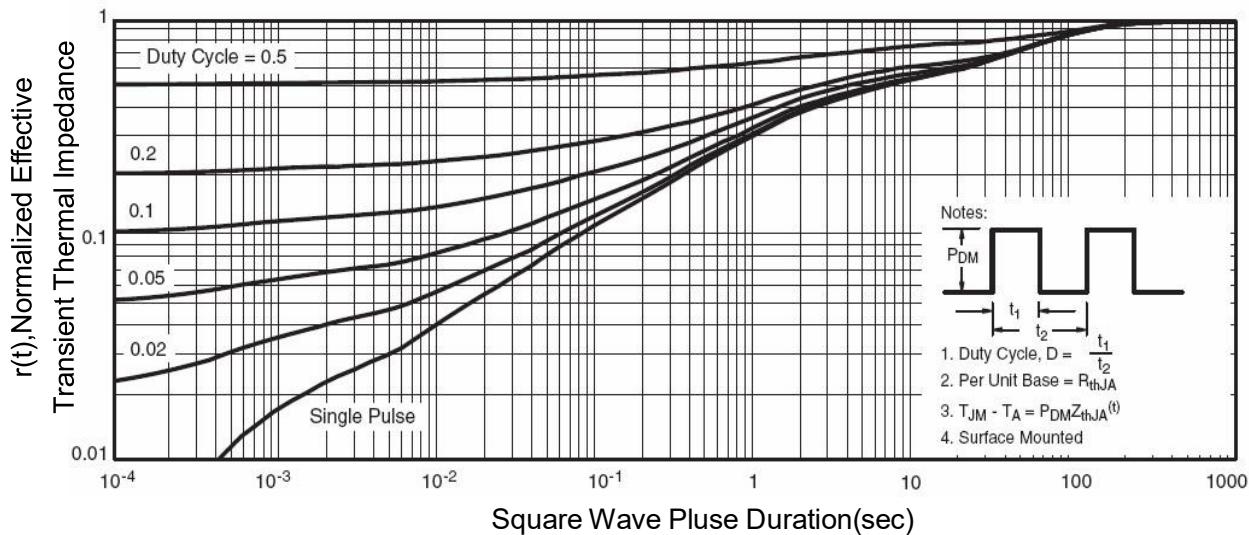
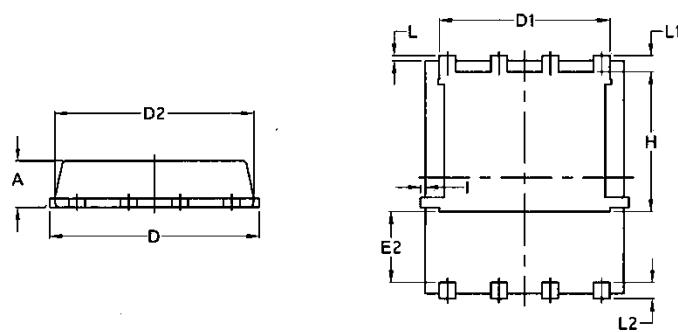
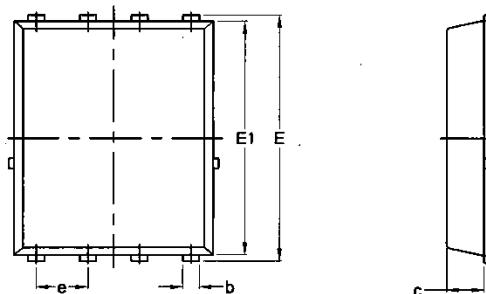


Figure 12 Source-Drain Diode Forward

**Figure 13 Safe Operation Area****Figure 14 Normalized Maximum Transient Thermal Impedance**

Package Mechanical Data-DFN5*6-8L-JQ Single


Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070